

AOL1436
N-Channel Enhancement Mode Field Effect Transistor
General Description

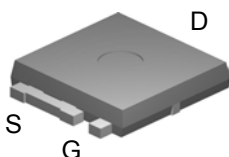
The AOL1436 uses advanced trench technology to provide excellent $R_{DS(ON)}$, shoot-through immunity and body diode characteristics. This device is ideally suited for use as a High side switch in CPU core power conversion. *Standard Product AOL1436 is Pb-free (meets ROHS & Sony 259 specifications).*

Features

$V_{DS} (V) = 25V$
 $I_D = 50A (V_{GS} = 10V)$
 $R_{DS(ON)} < 6m\Omega (V_{GS} = 20V)$
 $R_{DS(ON)} < 8.2m\Omega (V_{GS} = 12V)$
 $R_{DS(ON)} < 11.5m\Omega (V_{GS} = 10V)$

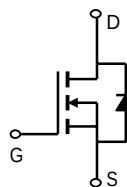
UIS Tested!
Rg,Ciss,Coss,Crss Tested!

Ultra SO-8™ Top View



Fits SOIC8 footprint !

Bottom tab connected to drain


Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ^B	I_D	$T_C=25^\circ C^G$	A
		$T_C=100^\circ C$	
Pulsed Drain Current ^C	I_{DM}	120	
Continuous Drain Current ^A	I_{DSM}	$T_A=25^\circ C$	A
		$T_A=70^\circ C$	
Avalanche Current ^C	I_{AR}	28	A
Repetitive avalanche energy $L=0.3mH^C$	E_{AR}	118	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ C$	W
		$T_C=100^\circ C$	
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ C$	W
		$T_A=70^\circ C$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ C$

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10s$	$R_{\theta JA}$	20	25	$^\circ C/W$
Maximum Junction-to-Ambient ^A	Steady-State		46	55	$^\circ C/W$
Maximum Junction-to-Case ^D	Steady-State	$R_{\theta JC}$	2.5	3.5	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	25			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±30V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2	3.2	4	V
I _{D(ON)}	On state drain current	V _{GS} =12V, V _{DS} =5V	120			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =20V, I _D =20A		5	6	mΩ
		V _{GS} =12V, I _D =20A		6.6	8.2	mΩ
		V _{GS} =10V, I _D =20A		8.6	11.5	mΩ
		T _J =125°C		11		mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		43		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.72	1	V
I _S	Maximum Body-Diode Continuous Current				50	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =12.5V, f=1MHz		1100	1350	pF
C _{oss}	Output Capacitance			420		pF
C _{rss}	Reverse Transfer Capacitance			200		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.8	1.5	Ω
SWITCHING PARAMETERS						
Q _g (12V)	Total Gate Charge	V _{GS} =10V, V _{DS} =12.5V, I _D =20A		20	24	nC
Q _g (10V)	Total Gate Charge			17		
Q _{gs}	Gate Source Charge			6.5		nC
Q _{gd}	Gate Drain Charge			6.8		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =12.5V, R _L =0.68Ω, R _{GEN} =0.6Ω		9.5		ns
t _r	Turn-On Rise Time			13.5		ns
t _{D(off)}	Turn-Off DelayTime			11.5		ns
t _f	Turn-Off Fall Time			5.4		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=100A/μs		32		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=100A/μs		19		nC

A. The value of R_{θJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on t<10s R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 us pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is limited by bond-wires.

H. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

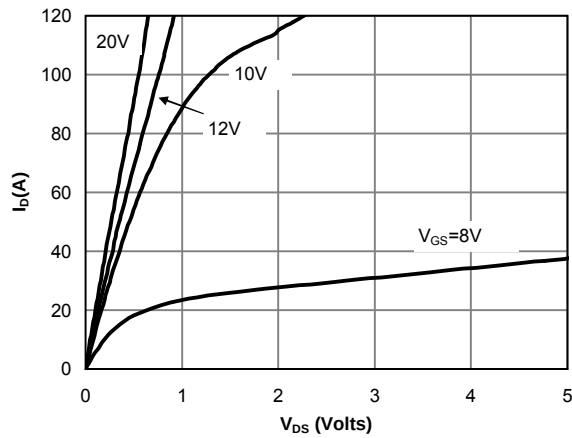


Figure 1: On-Region Characteristics

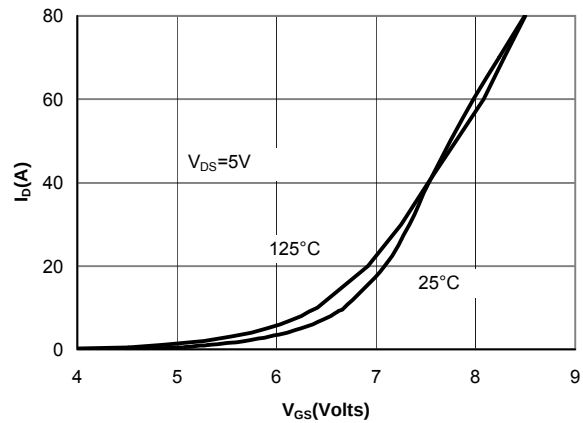


Figure 2: Transfer Characteristics

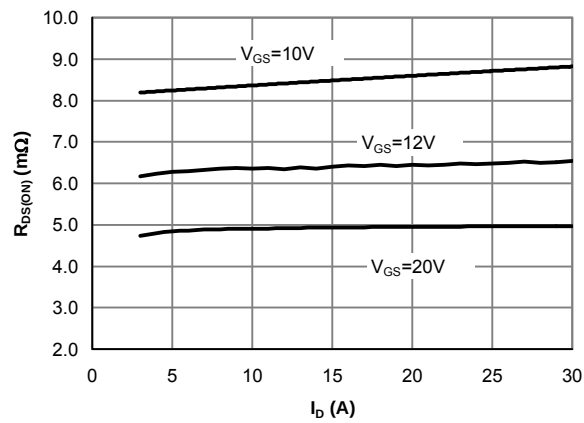


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

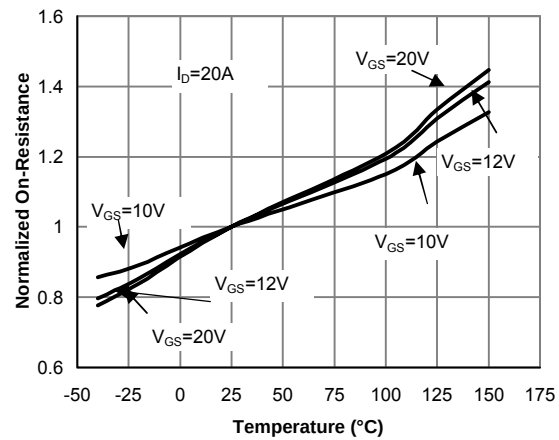


Figure 4: On-Resistance vs. Junction Temperature

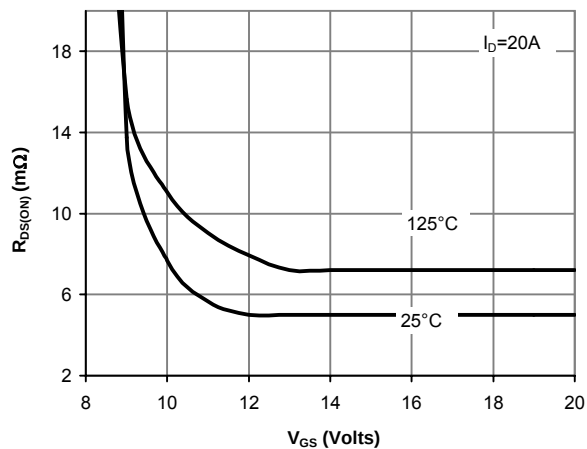


Figure 5: On-Resistance vs. Gate-Source Voltage

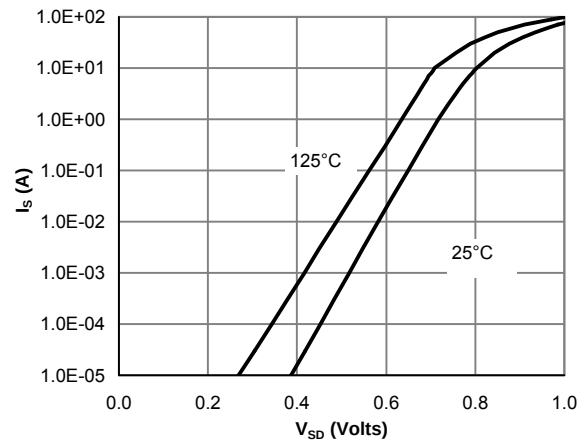


Figure 6: Body-Diode Characteristics

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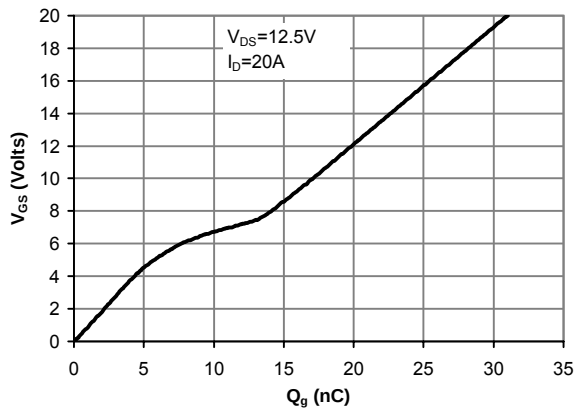


Figure 7: Gate-Charge Characteristics

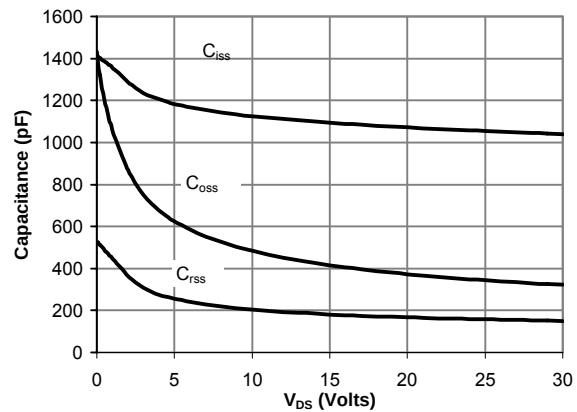


Figure 8: Capacitance Characteristics

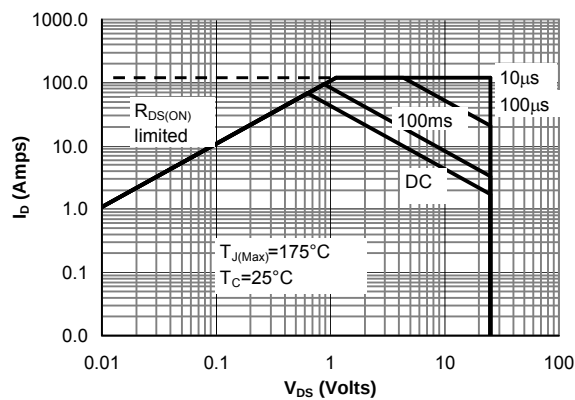


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

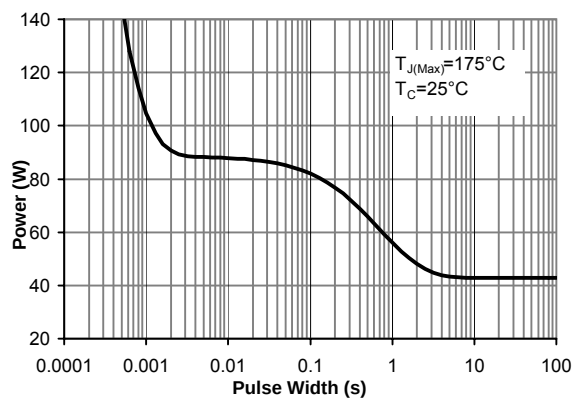


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

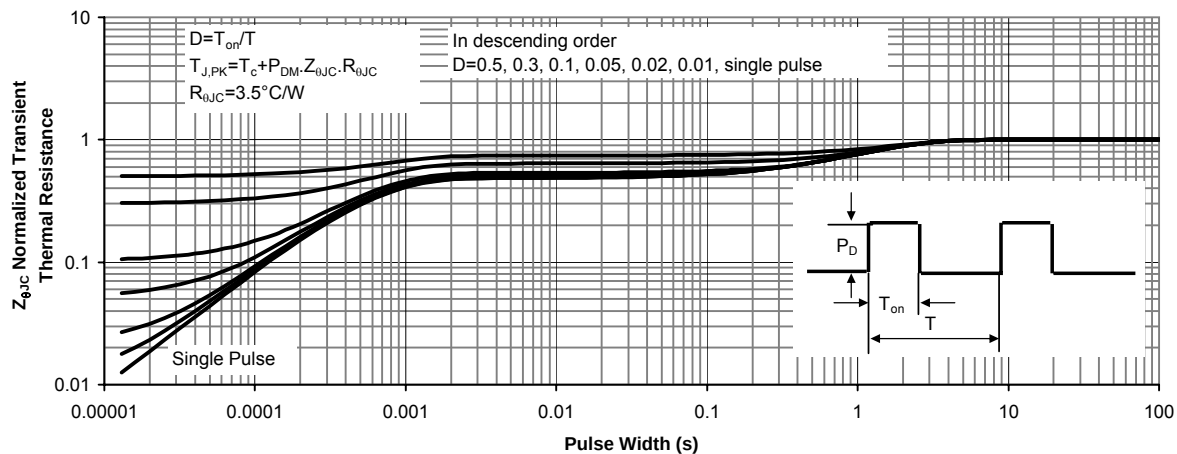


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

